

MATERIAL FOR FORMING HAFNIUM-BASED OXIDE FILM

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Inventor(s): MACHIDA HIDEAKI; HOSHINO ASAKO
Applicant(s): TRI CHEMICAL LABORATORY INC
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Abstract

PROBLEM TO BE SOLVED: To efficiently provide a technique for forming a neat hafnium-based film.
SOLUTION: A compound which is expressed by a chemical formula (R₁R₂N)₄ Hf is used.

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